

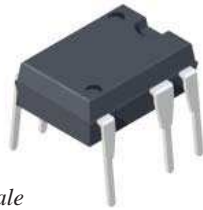
PWM Off-Line Switching Regulator ICs

Features and Benefits

- Current mode PWM control
- Brown-In and Brown-Out function: auto-restart, prevents excess input current and heat rise at low input voltage
- Auto Standby function: improves efficiency by Burst mode operation in light load
 - Normal load operation: PWM mode
 - Light load operation: Burst mode
- No load power consumption < 25 mW
- Operating frequency, $f_{OSC(AVG)}(typ) = 67 \text{ kHz}$
- Random Switching function: reduces EMI noise, and simplifies EMI filters
- Slope Compensation function: avoids subharmonic oscillation
- Leading Edge Blanking function

Continued on the next page...

Package: DIP8



Not to scale

Description

The STR-A6051M, STR-A6052M, STR-A6053M, and STR-A6079M are power ICs for switching power supplies, incorporating a power MOSFET and a current mode PWM controller IC in one package.

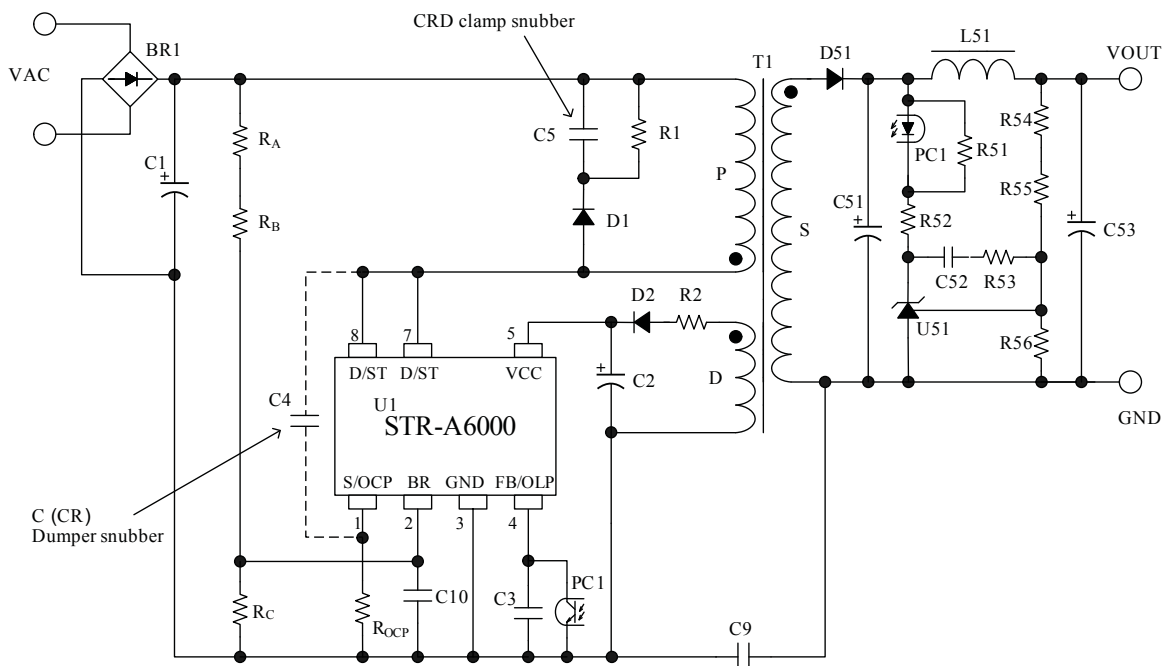
To achieve low power consumption, these products include a startup circuit and a standby function in the controller. The switching modes are automatically changed according to load conditions: in normal operation, PWM mode, and in light load conditions, burst mode. The rich set of protection features helps to realize low component counts, and high performance-to-cost power supply.

Applications:

Switching power supplies for electronic devices such as:

- Battery charger
- Standby power supply
- Small switch-mode power supply (SMPS)
- Auxiliary power supply for controller

Typical Application Circuit



Features and Benefits (continued)

- Audible Noise Suppression function during Standby mode
- Protection features
 - Overcurrent protection (OCP): pulse-by-pulse, with input compensation function
 - Overvoltage protection (OVP): latched shutdown
 - Overload protection (OLP): auto-restart, with timer
 - Thermal shutdown protection (TSD): latched shutdown

Selection Guide

Part Number	Power MOSFET		Output Power*, P _{OUT} (W)			
	V _{DSS} (min) (V)	R _{DS(ON)} (max) (Ω)	Open Frame		Adaptor	
			230 VAC	85 to 265 VAC	230 VAC	85 to 265 VAC
STR-A6051M	650	3.95	30	21	20	16
STR-A6052M	650	2.8	35	25	23	19
STR-A6053M	650	1.9	41	29	26	22
STR-A6079M	800	19.2	13	9	8	6

*The listed output power is based on the thermal ratings, and the peak output power can be 120% to 140% of the value stated here. At low output voltage and short duty cycle, the output power may be less than the value stated here.

The polarity value for current specifies a sink as "+," and a source as "–," referencing the IC.

Absolute Maximum Ratings Unless otherwise specified, T_A = 25°C

Characteristic	Symbol	Notes	Pins	Rating	Unit		
Drain Peak Current ¹	I _{DPEAK}	STR-A6051M	Single pulse	8 – 1	2.5	A	
		STR-A6052M			3.0	A	
		STR-A6053M			4.0	A	
		STR-A6079M			1.2	A	
Avalanche Energy ²	E _{AS}	STR-A6051M	Single pulse, V _{DD} = 99 V, L = 20 mH, I _{LPEAK} = 2 A	8 – 1	47	mJ	
		STR-A6052M			Single pulse, V _{DD} = 99 V, L = 20 mH, I _{LPEAK} = 2.3 A	62	mJ
		STR-A6053M			Single pulse, V _{DD} = 99 V, L = 20 mH, I _{LPEAK} = 2.7 A	86	mJ
		STR-A6079M			Single pulse, V _{DD} = 99 V, L = 20 mH, I _{LPEAK} = 1.2 A	7	mJ
S/OCP Pin Voltage	V _{OCP}		1 – 3	–2 to 6	V		
Control Part Input Voltage	V _{CC}		5 – 3	32	V		
FB/OLP Pin Voltage	V _{FB}		4 – 3	–0.3 to 14	V		
FB/OLP Pin Sink Current	I _{FB}		4 – 3	1.0	mA		
BR Pin Voltage	V _{BR}		2 – 3	–0.3 to 7	V		
BR Pin Sink Current	I _{BR}		2 – 3	1.0	mA		
Power Dissipation of MOSFET ³	P _{D1}	Mounted on 15 mm × 15 mm printed circuit board	8 – 1	1.35	W		
Power Dissipation of Control Part	P _{D2}		5 – 3	1.2	W		
Operating Ambient Temperature ⁴	T _{OP}		–	–20 to 125	°C		
Storage Temperature	T _{stg}		–	–40 to 125	°C		
Channel Temperature	T _{ch}		–	150	°C		

¹Refer to MOSFET Safe Operating Area Curve.

²Refer to MOSFET Avalanche Energy Derating Coefficient Curve.

³Refer to MOSFET Temperature versus Power Dissipation Curve.

⁴The recommended internal frame temperature, T_F, is 115°C (max).

Electrical Characteristics of Control Part Unless otherwise specified, $T_A = 25^\circ\text{C}$, $V_{CC} = 18\text{ V}$

Characteristic	Symbol	Test Conditions	Pins	Min.	Typ.	Max.	Unit
Operation Start Voltage	$V_{CC(ON)}$		5 - 3	13.8	15.3	16.8	V
Operation Stop Voltage ¹	$V_{CC(OFF)}$		5 - 3	7.3	8.1	8.9	V
Circuit Current in Operation	$I_{CC(ON)}$	$V_{CC} = 12\text{ V}$	5 - 3	–	–	2.5	mA
Minimum Start Voltage	$V_{ST(ON)}$		5 - 3	–	38	–	V
Startup Current	$I_{STARTUP}$	$V_{CC} = 13.5\text{ V}$	5 - 3	-3.7	-2.5	-1.5	mA
Startup Current Threshold Biasing Voltage ¹	$V_{CC(BIAS)}$	$I_{CC} = -100\ \mu\text{A}$	5 - 3	8.5	9.5	10.5	V
Average Operation Frequency	$f_{OSC(AVG)}$		8 - 3	60	67	74	kHz
Frequency Modulation Deviation	Δf		8 - 3	–	5	–	kHz
Maximum Duty Cycle	D_{MAX}		8 - 3	77	83	89	%
Minimum On-Time	$t_{ON(MIN)}$		–	–	540	–	ns
Leading Edge Blanking Time	t_{BW}		–	–	340	–	ns
OCP Compensation Coefficient	DPC		–	–	20	–	mV/ μs
OCP Compensation Duty Cycle Limit	D_{DPC}		–	–	36	–	%
OCP Threshold Voltage at Zero Duty Cycle	$V_{OCP(L)}$		1 - 3	0.70	0.78	0.86	V
OCP Threshold Voltage at 36% Duty Cycle	$V_{OCP(H)}$	$V_{CC} = 32\text{ V}$	1 - 3	0.81	0.9	0.99	V
Maximum Feedback Current	$I_{FB(MAX)}$	$V_{CC} = 12\text{ V}$	4 - 3	-340	-230	-150	μA
Minimum Feedback Current	$I_{FB(MIN)}$		4 - 3	-30	-15	-7	μA
FB/OLP Pin Oscillation Stop Threshold Voltage	$V_{FB(STB)}$		4 - 3	0.85	0.95	1.05	V
OLP Threshold Voltage	$V_{FB(OLP)}$		4 - 3	7.3	8.1	8.9	V
OLP Delay Time	t_{OLP}		4 - 3	54	68	82	ms
OLP Operation Current	$I_{CC(OLP)}$	$V_{CC} = 12\text{ V}$	5 - 3	–	300	600	μA
FB/OLP Pin Clamp Voltage	$V_{FB(CLAMP)}$		4 - 3	11	12.8	14	V
Brown-In Threshold Voltage	$V_{BR(IN)}$	$V_{CC} = 32\text{ V}$	2 - 3	5.2	5.6	6	V
Brown-Out Threshold Voltage	$V_{BR(OUT)}$	$V_{CC} = 32\text{ V}$	2 - 3	4.45	4.8	5.15	V
BR Pin Clamp Voltage	$V_{BR(CLAMP)}$	$V_{CC} = 32\text{ V}$	2 - 3	6	6.4	7	V
BR Function Disabling Threshold Voltage	$V_{BR(DIS)}$	$V_{CC} = 32\text{ V}$	2 - 3	0.3	0.48	0.7	V
VCC Pin OVP Threshold Voltage	$V_{CC(OVP)}$		5 - 3	26	29	32	V
Latch Circuits Holding Current ²	$I_{CC(LATCH)}$	$V_{CC} = 9.5\text{ V}$	5 - 3	–	700	–	μA
Thermal Shutdown Temperature	$T_{J(TSD)}$		–	135	–	–	$^\circ\text{C}$

¹ $V_{CC(BIAS)} > V_{CC(OFF)}$ always.

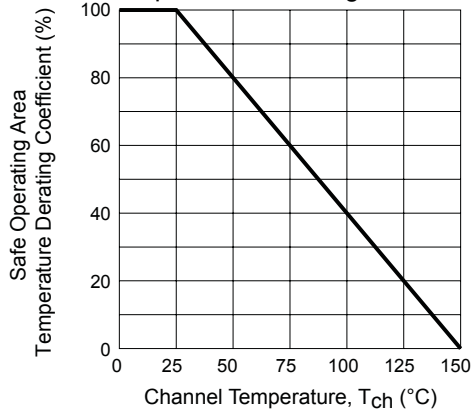
²A latch circuit is a circuit operated with Overvoltage Protection (OVP) and/or Thermal Shutdown Protection (TSD) in operation.

Electrical Characteristics of MOSFET Unless otherwise specified, T_A is 25°C

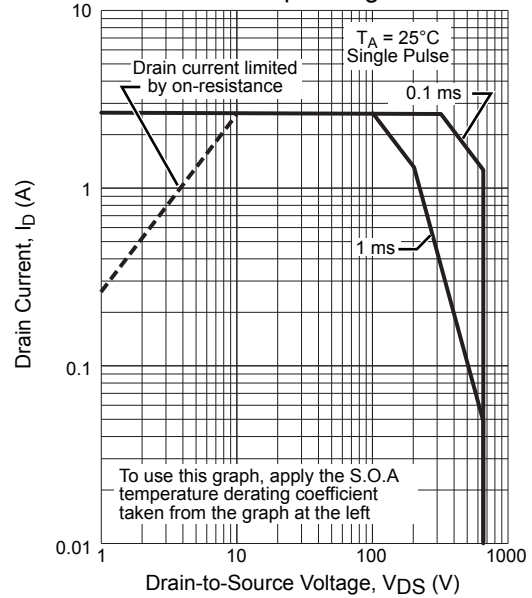
Characteristic	Symbol	Test Conditions	Pins	Min.	Typ.	Max.	Unit
Drain-to-Source Breakdown Voltage	V_{DSS}	STR-A6051M STR-A6052M STR-A6053M	8 – 1	650	–	–	V
		STR-A6079M		800	–	–	V
Drain Leakage Current	I_{DSS}		8 – 1	–	–	300	μ A
On-Resistance	$R_{DS(ON)}$	STR-A6051M	8 – 1	–	–	3.95	Ω
		STR-A6052M		–	–	2.8	Ω
		STR-A6053M		–	–	1.9	Ω
		STR-A6079M		–	–	19.2	Ω
Switching Time	t_f	STR-A6051M STR-A6052M STR-A6053M	8 – 1	–	–	250	ns
		STR-A6079M		–	–	400	ns
Thermal Resistance	$R_{\theta ch-C}$	The thermal resistance between the channels of the MOSFET and the case. Case temperature, T_C , is measured at the center of the case top surface.	–	–	–	22	$^{\circ}$ C/W

**Characteristic Performance
STR-A6051M**

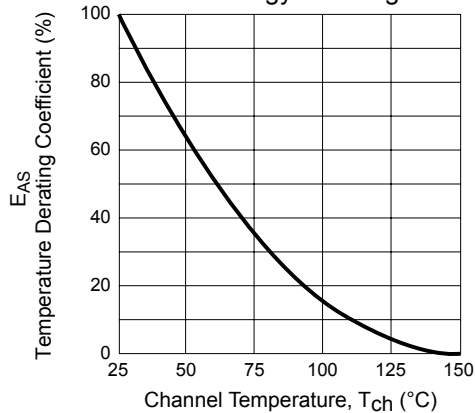
S. O. A. Temperature Derating Coefficient Curve



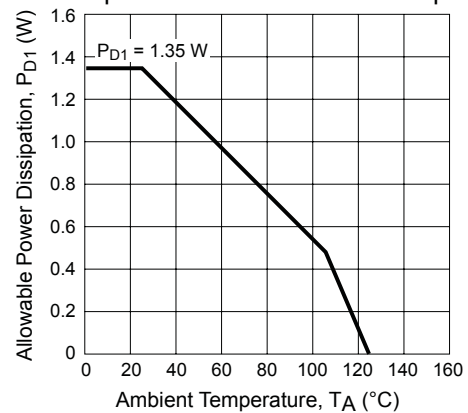
MOSFET Safe Operating Area Curve



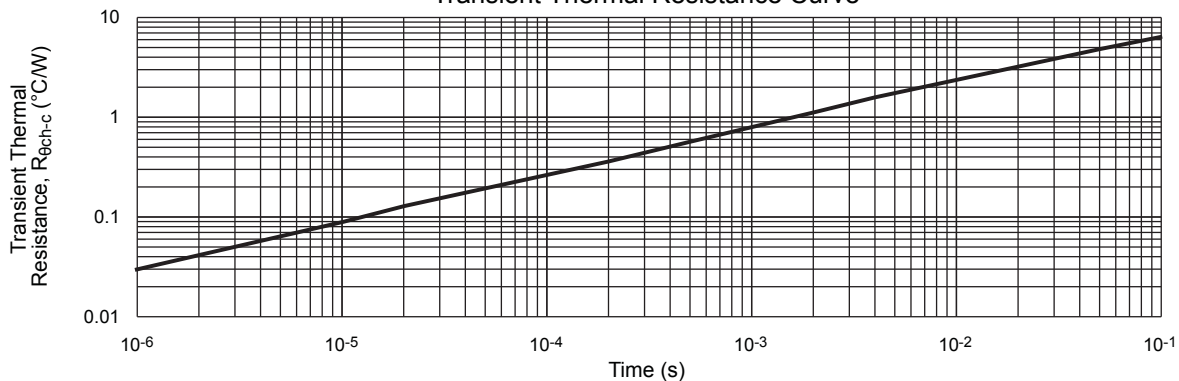
MOSFET Avalanche Energy Derating Coefficient Curve



MOSFET Temperature versus Power Dissipation Curve

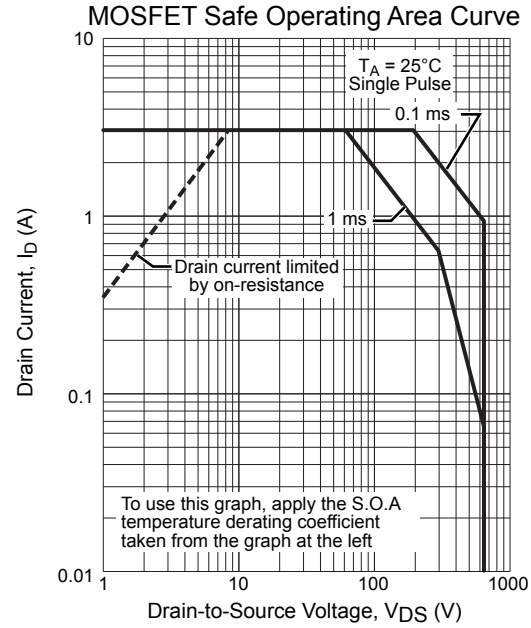
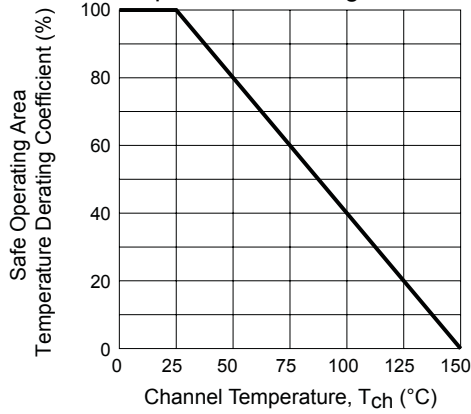


Transient Thermal Resistance Curve

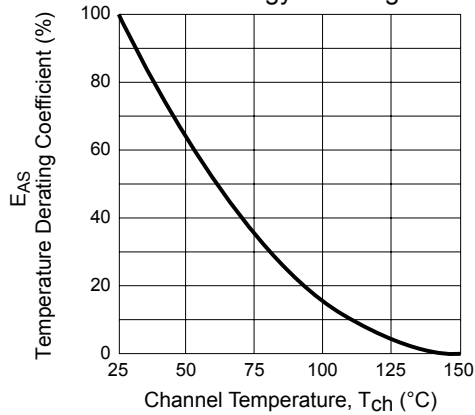


**Characteristic Performance
STR-A6052M**

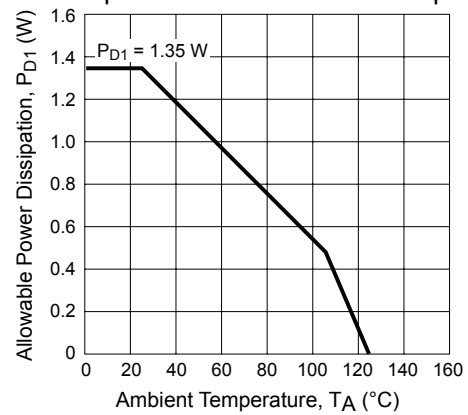
S. O. A. Temperature Derating Coefficient Curve



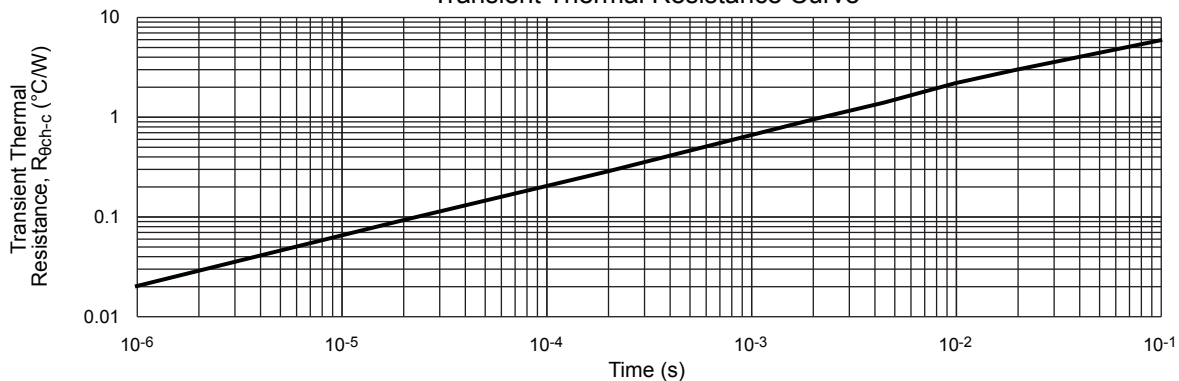
MOSFET Avalanche Energy Derating Coefficient Curve



MOSFET Temperature versus Power Dissipation Curve

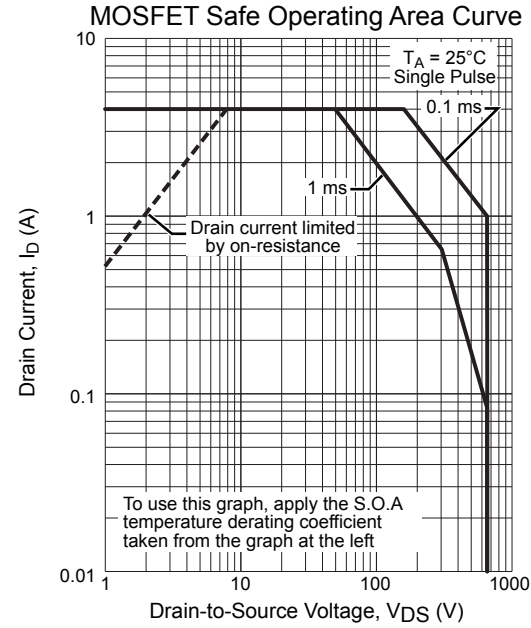
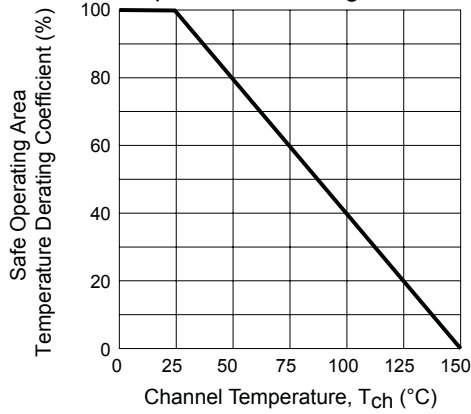


Transient Thermal Resistance Curve

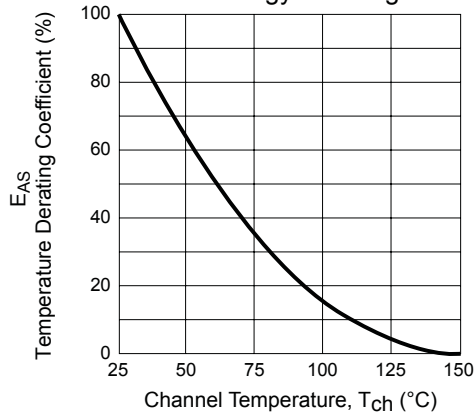


**Characteristic Performance
STR-A6053M**

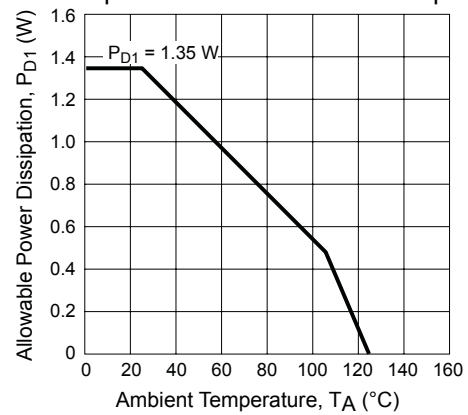
S. O. A. Temperature Derating Coefficient Curve



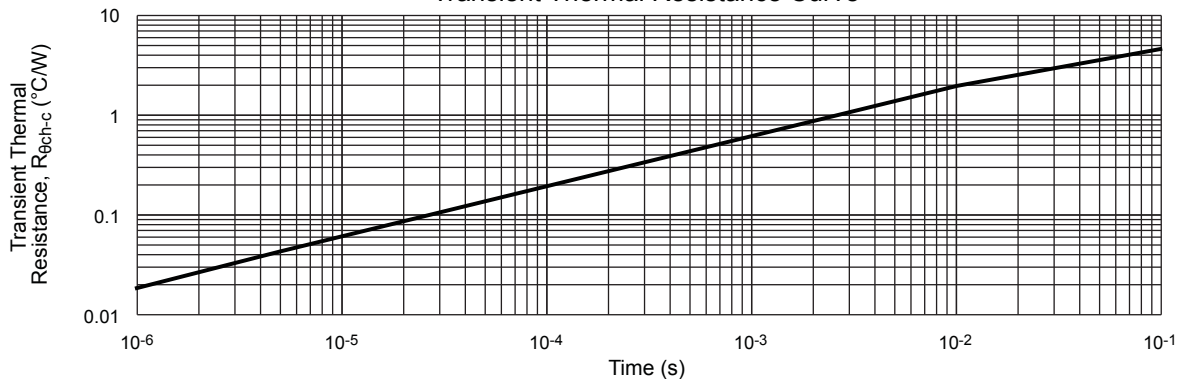
MOSFET Avalanche Energy Derating Coefficient Curve



MOSFET Temperature versus Power Dissipation Curve

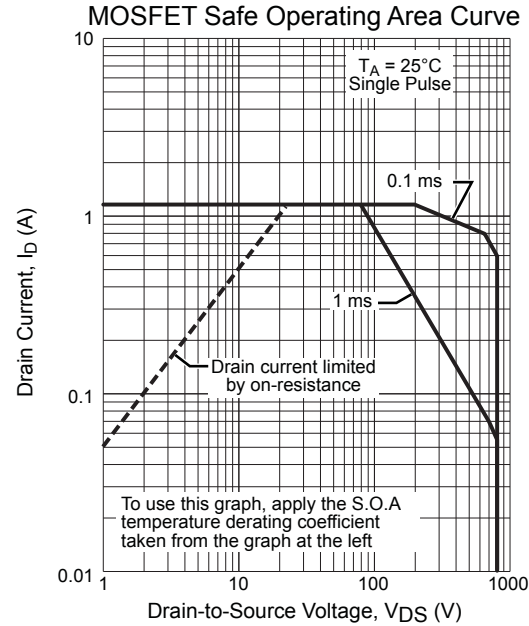
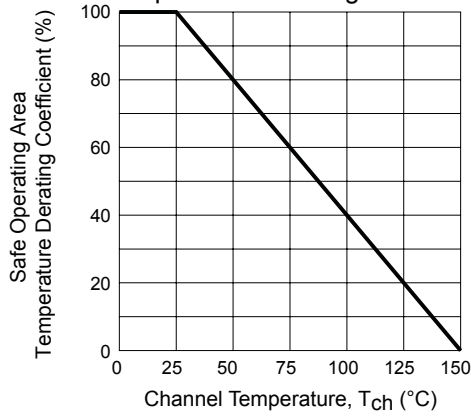


Transient Thermal Resistance Curve

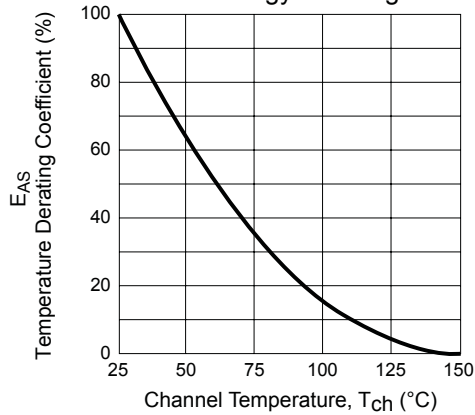


**Characteristic Performance
STR-A6079M**

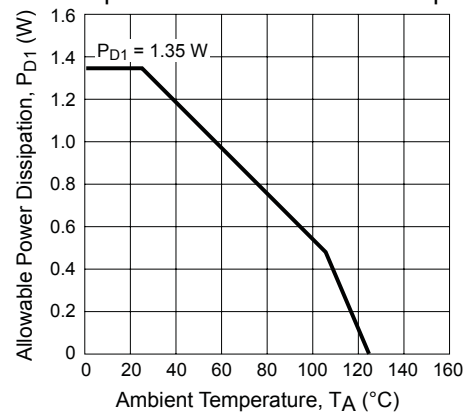
S. O. A. Temperature Derating Coefficient Curve



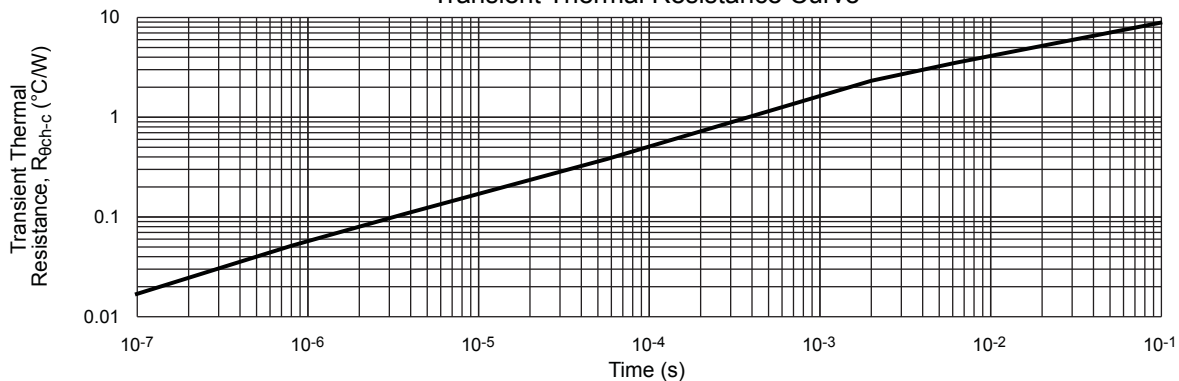
MOSFET Avalanche Energy Derating Coefficient Curve



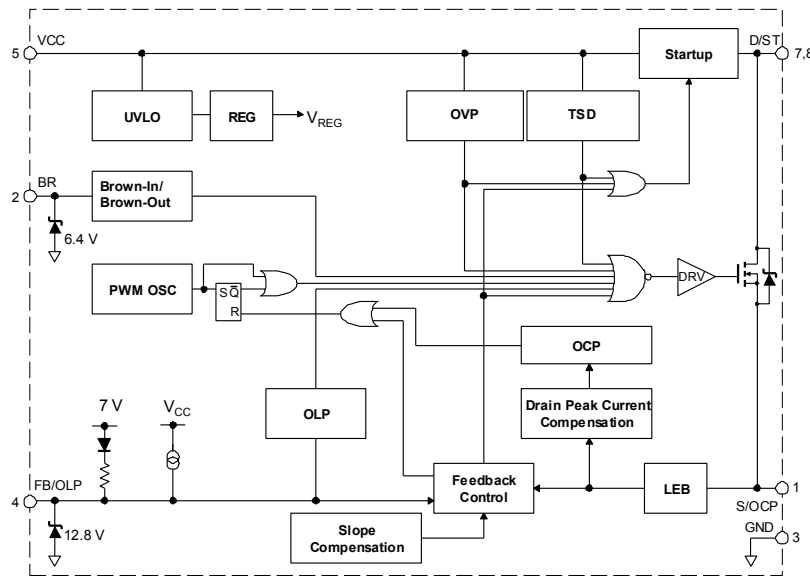
MOSFET Temperature versus Power Dissipation Curve



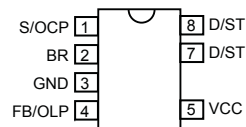
Transient Thermal Resistance Curve



Functional Block Diagram



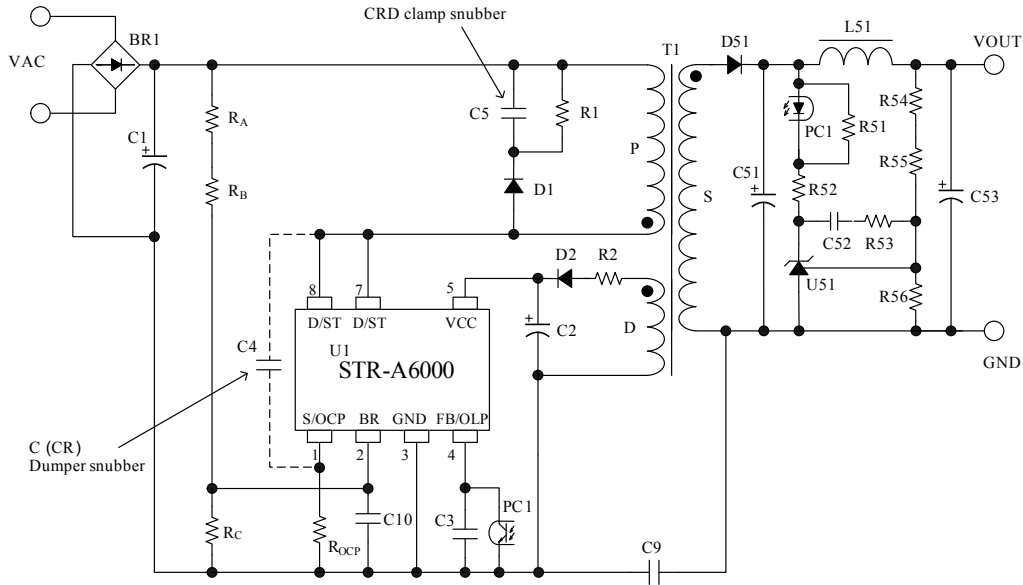
Pin-out Diagram



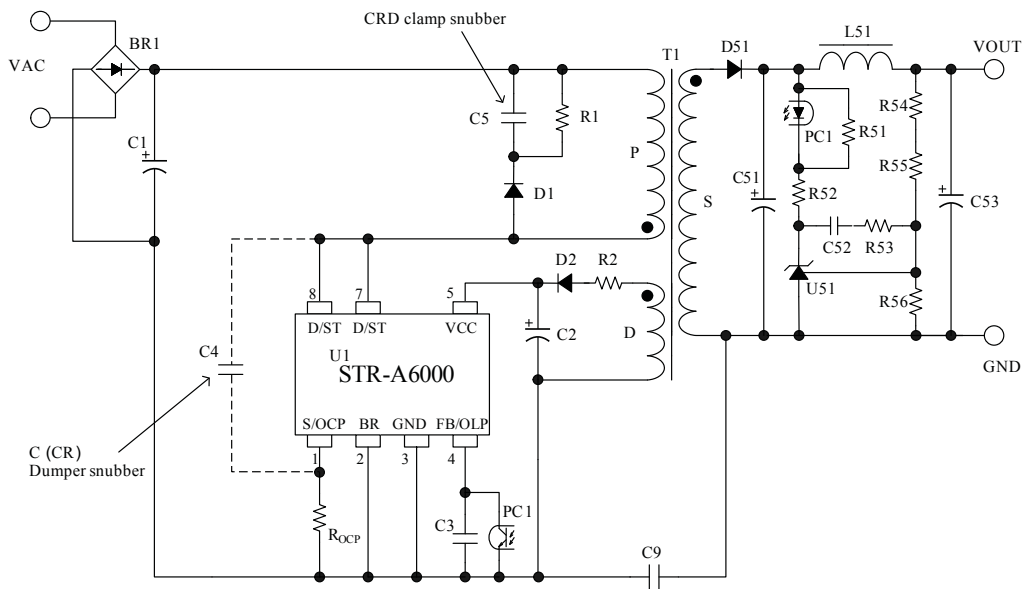
Pin List Table

Number	Name	Function
1	S/OCP	MOSFET source, and input for Overcurrent Protection (OCP) signal
2	BR	Input for Brown-In and Brown-Out detection voltage
3	GND	Ground
4	FB/OLP	Feedback signal input for constant voltage control signal, and input of Overload Protection (OLP) signal
5	VCC	Power supply voltage input for Control Part and input of Overvoltage Protection (OVP) signal
6	—	(Pin removed)
7, 8	D/ST	MOSFET drain, and input of the startup current

Typical Application Circuits



Typical application circuit example, enabled Brown-In/Brown-Out function (DC line detection)



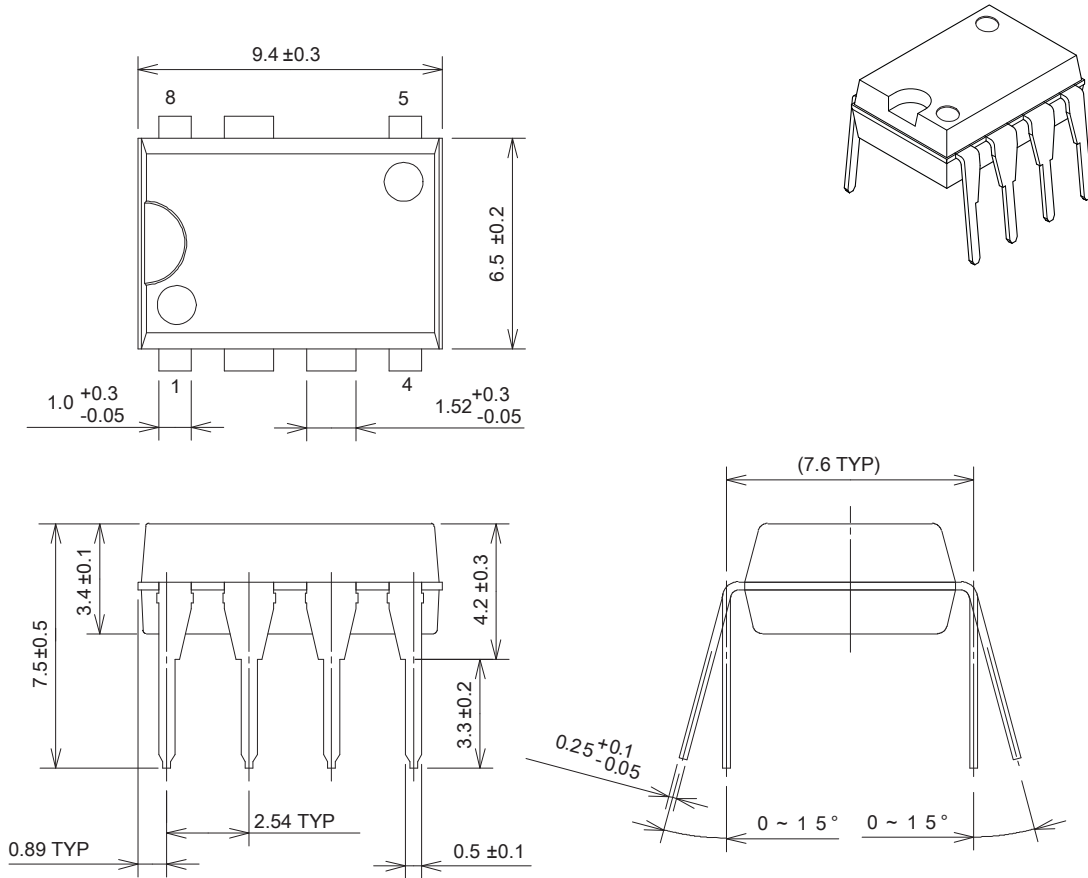
Typical application circuit example, disabled Brown-In/Brown-Out function

STR-A6000M Series

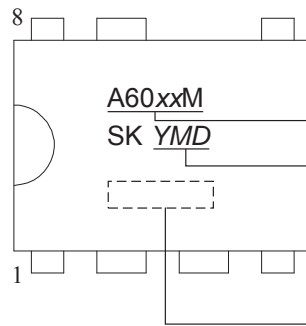
PWM Off-Line Switching Regulator ICs

Package Diagram

- DIP8 package
- The following show a representative type of DIP8.
- The pin 6 is removed to provide greater creepage and clearance isolation between the high voltage pins (pins 7 and 8: D/ST) and the low voltage pin (pin 5: VCC).



Unit: mm



Part Number

Lot Number

Y is the last digit of the year (0 to 9)

M is the month (1 to 9, O, N, or D)

D is a period of days (1 to 3):

1 – 1st to 10th

2 – 11th to 20th

3 – 21st to 31st

Sanken Control Number



Device composition compliant with the RoHS directive.

Operating Precautions

In the case that you use Sanken products or design your products by using Sanken products, the reliability largely depends on the degree of derating to be made to the rated values. Derating may be interpreted as a case that an operation range is set by derating the load from each rated value or surge voltage or noise is considered for derating in order to assure or improve the reliability. In general, derating factors include electric stresses such as electric voltage, electric current, electric power etc., environmental stresses such as ambient temperature, humidity etc. and thermal stress caused due to self-heating of semiconductor products. For these stresses, instantaneous values, maximum values and minimum values must be taken into consideration. In addition, it should be noted that since power devices or IC's including power devices have large self-heating value, the degree of derating of junction temperature affects the reliability significantly.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

Cautions for Storage

- Ensure that storage conditions comply with the standard temperature (5 to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting the products on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce excess stress.

- Volatile-type silicone greases may crack after long periods of time, resulting in reduced heat radiation effect. Silicone greases with low consistency (hard grease) may cause cracks in the mold resin when screwing the products to a heatsink.

Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Type	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials Inc.
SC102	Dow Corning Toray Co., Ltd.

Soldering

- When soldering the products, please be sure to minimize the working time, within the following limits:

260 ± 5 °C 10 ± 1 s (Flow, 2 times)

380 ± 10 °C 3.5 ± 0.5 s (Soldering iron, 1 time)

- Soldering should be at a distance of at least 1.5 mm from the body of the products.

Electrostatic Discharge

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1MΩ of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in order to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil.

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